

SCE 0110 -  
Elementos de Lógica Digital I

**Tecnologia de Implementação**

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# *Sumário*

- Como os transistores operam e formam comutadores/chaves simples
- Tecnologia de CI (Circuito Integrado)
- Portas lógicas CMOS

$V_{DD} = V_{CC}$ /positivo/tensão da fonte de alimentação (1 a 5V)

$V_{SS} = \text{Gnd}$ /negativo/ terra/comun (0V)

$V_{0,max}$  = tensão máxima para nível lógico 0

$V_{1,min}$  = tensão mínima para nível lógico 1

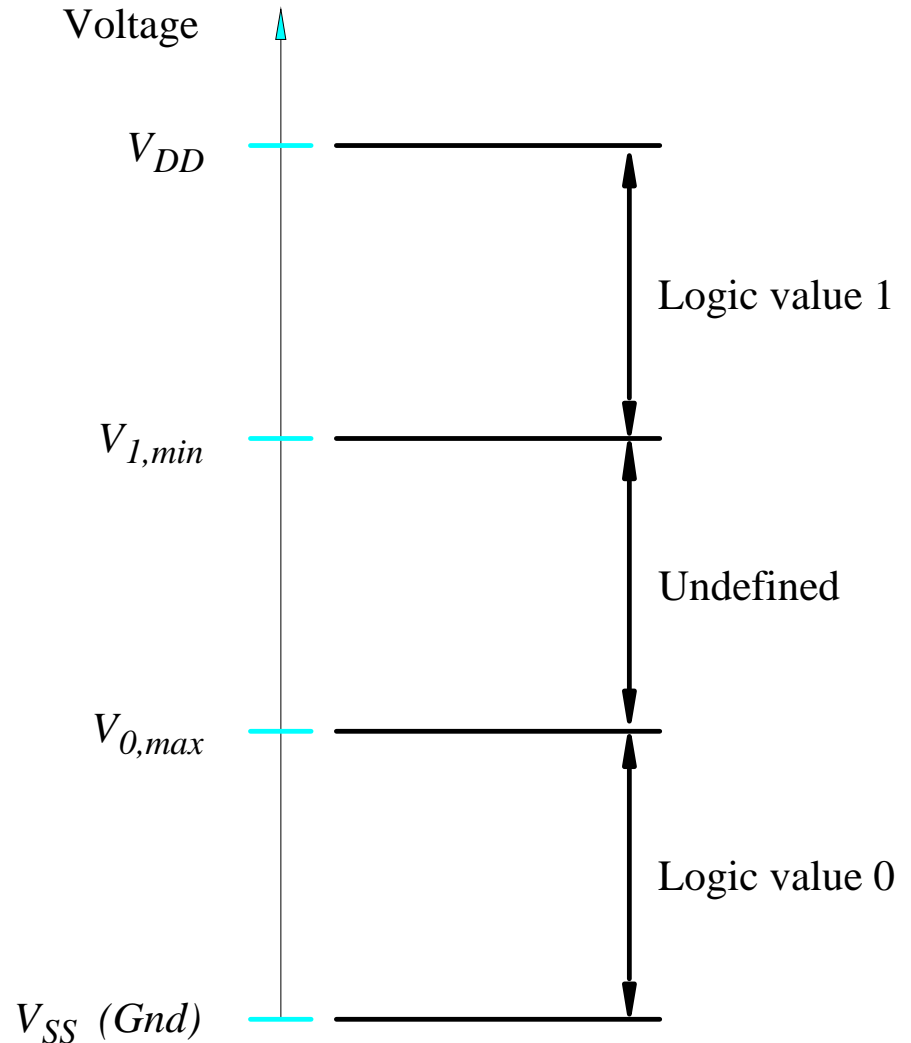
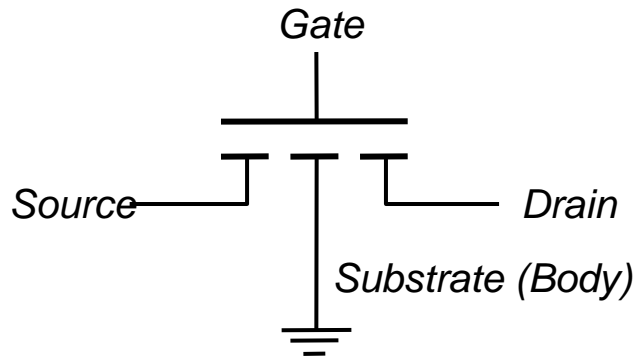


Figure 3.1. Logic values as voltage levels.

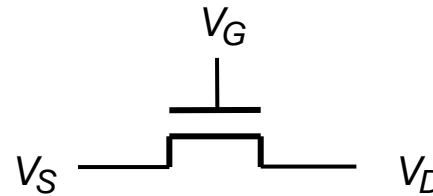
# MOSFET (Metal Oxide Semiconductor Field-Effect Transistor): NMOS (Canal N)



(a) A simple switch controlled by the input  $x$



(b) NMOS transistor



(c) Simplified symbol for an NMOS transistor

Figure 3.2. NMOS transistor as a switch.

# MOSFET (Metal Oxide Semiconductor Field-Effect Transistor): PMOS (Canal P)

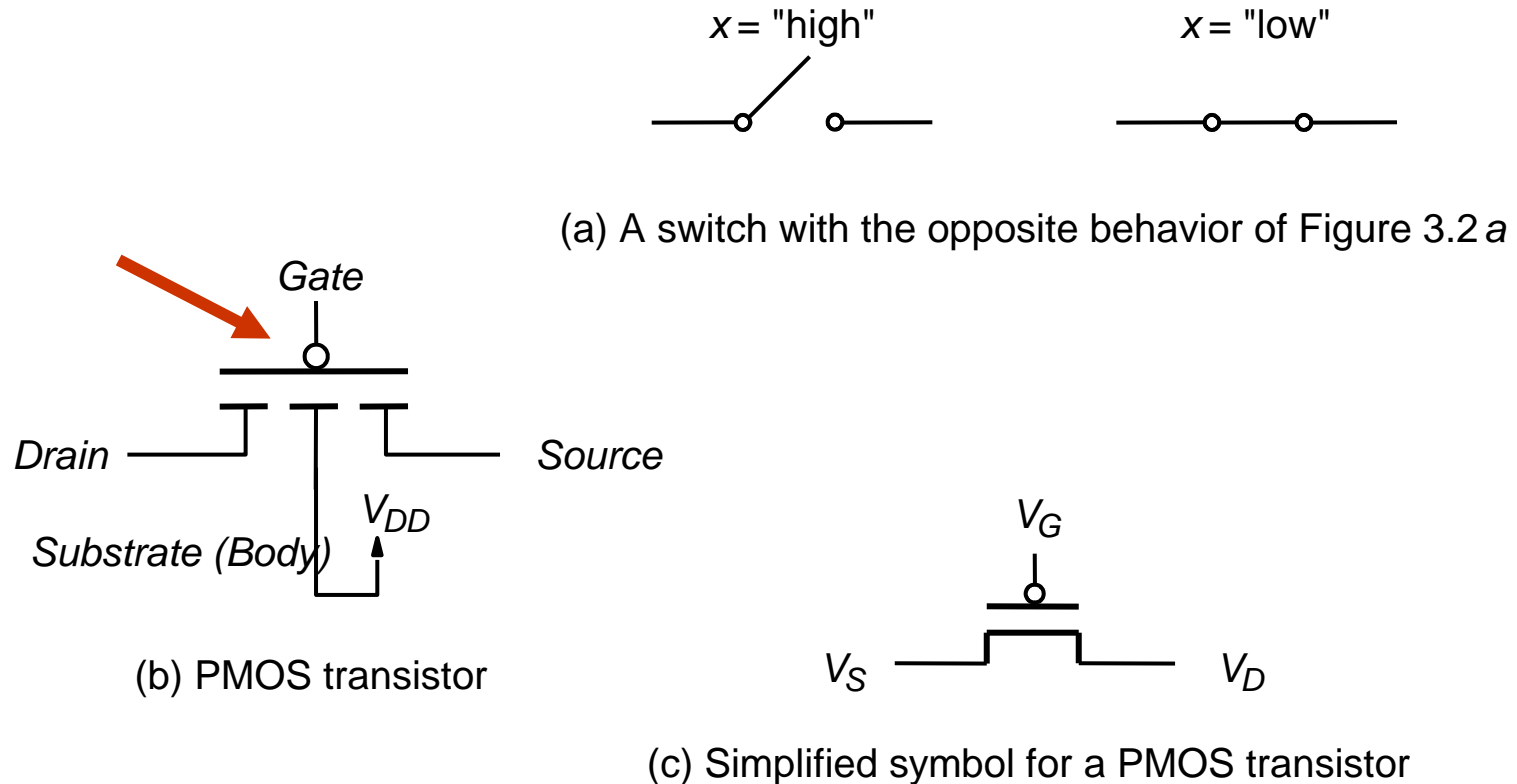
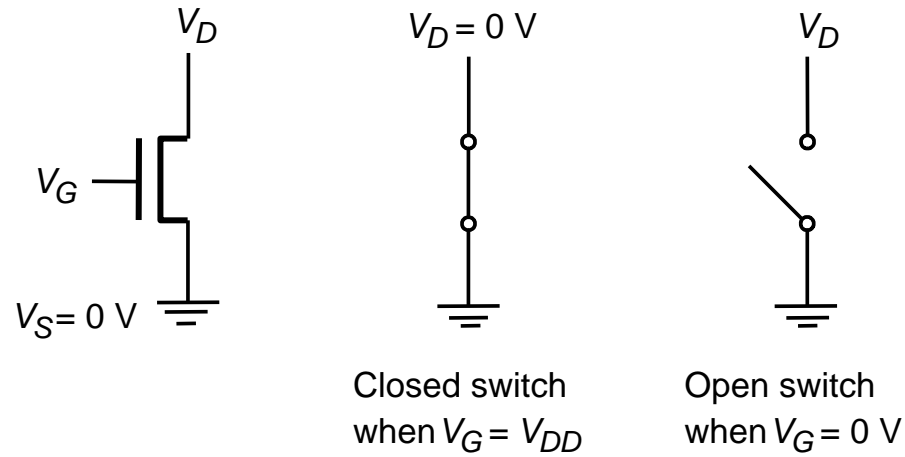
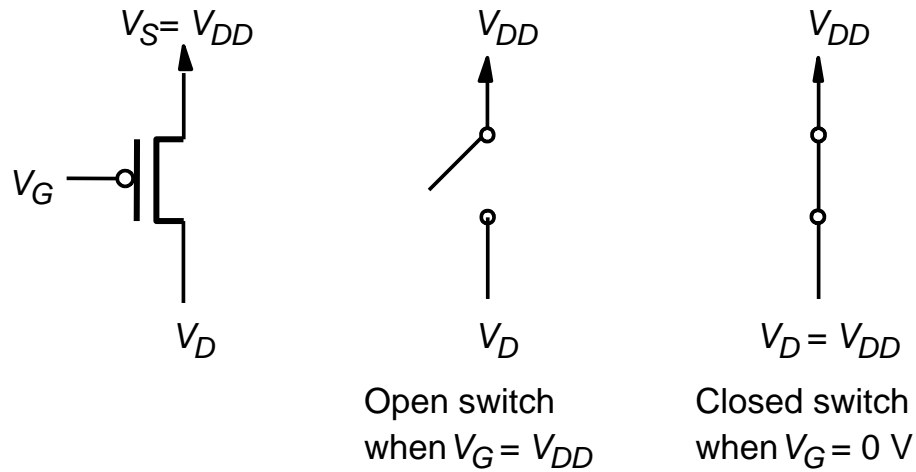


Figure 3.3. PMOS transistor as a switch.



(a) NMOS transistor

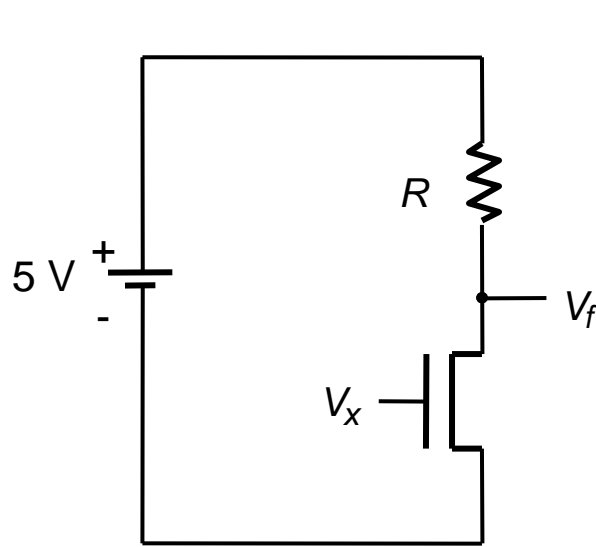


(b) PMOS transistor

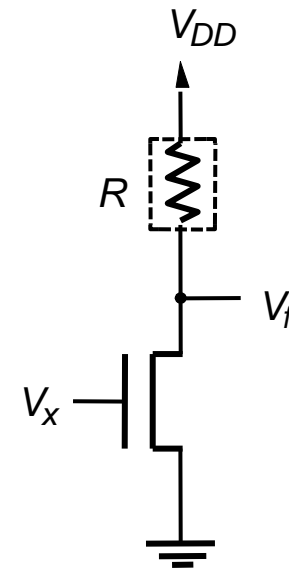
Figure 3.4. NMOS and PMOS transistors in logic circuits.

# *Histórico*

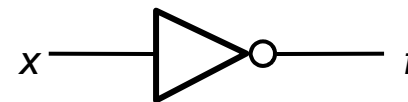
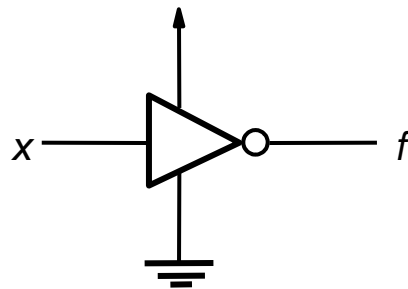
- A construção de portas lógicas com MOSFET tornou-se popular nos anos 70
- Nessa época utilizava-se NMOS ou PMOS, mas não ambas
- Desde os anos 80 passou-se a utilizar uma combinação de NMOS e PMOS, conhecida como CMOS (Complementary MOS)



(a) Circuit diagram



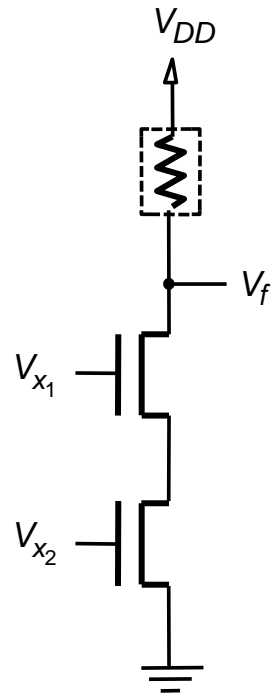
(b) Simplified circuit diagram



(c) Graphical symbols

Figure 3.5. A NOT gate built using NMOS technology.

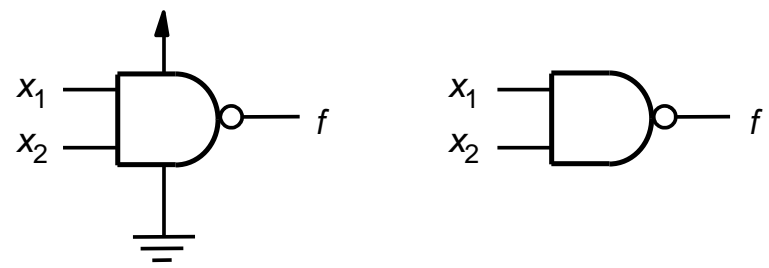




$x_1$	$x_2$	$f$
0	0	1
0	1	1
1	0	1
1	1	0

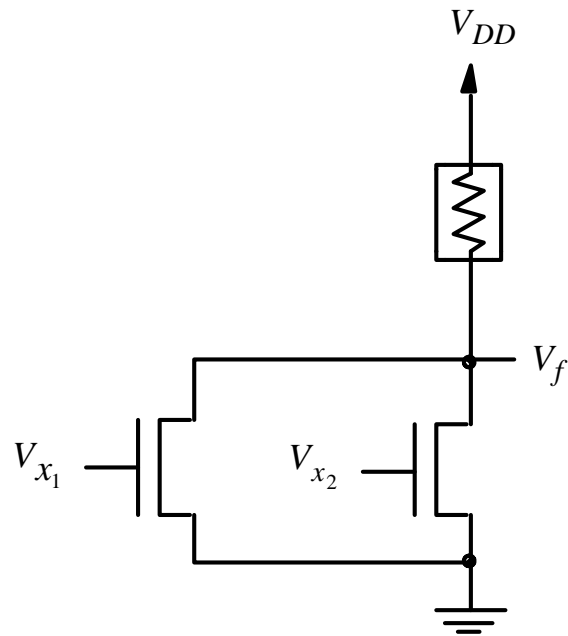
(a) Circuit

(b) Truth table



(c) Graphical symbols

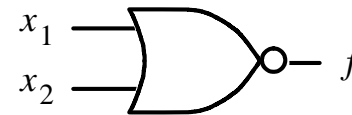
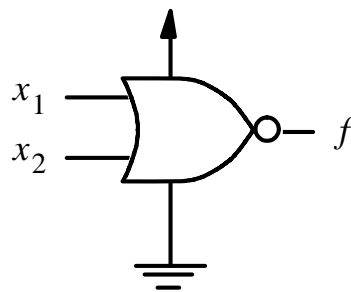
Figure 3.6. NMOS realization of a NAND gate.



(a) Circuit

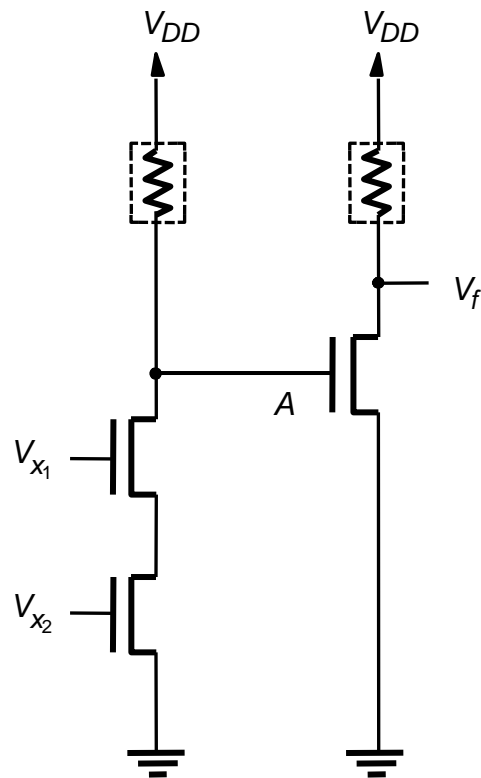
$x_1$	$x_2$	$f$
0	0	1
0	1	0
1	0	0
1	1	0

(b) Truth table



(c) Graphical symbols

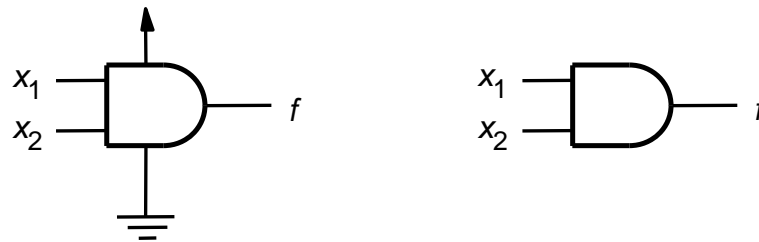
Figure 3.7. NMOS realization of a NOR gate.



(a) Circuit

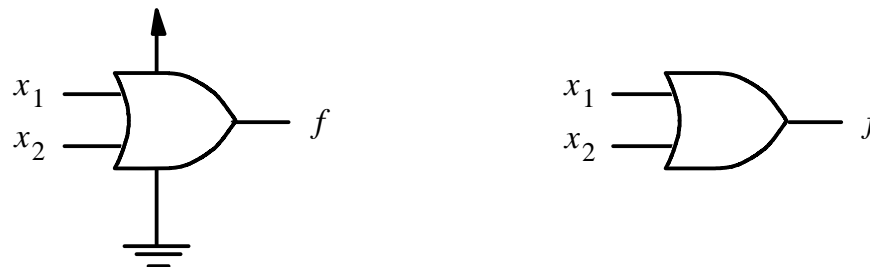
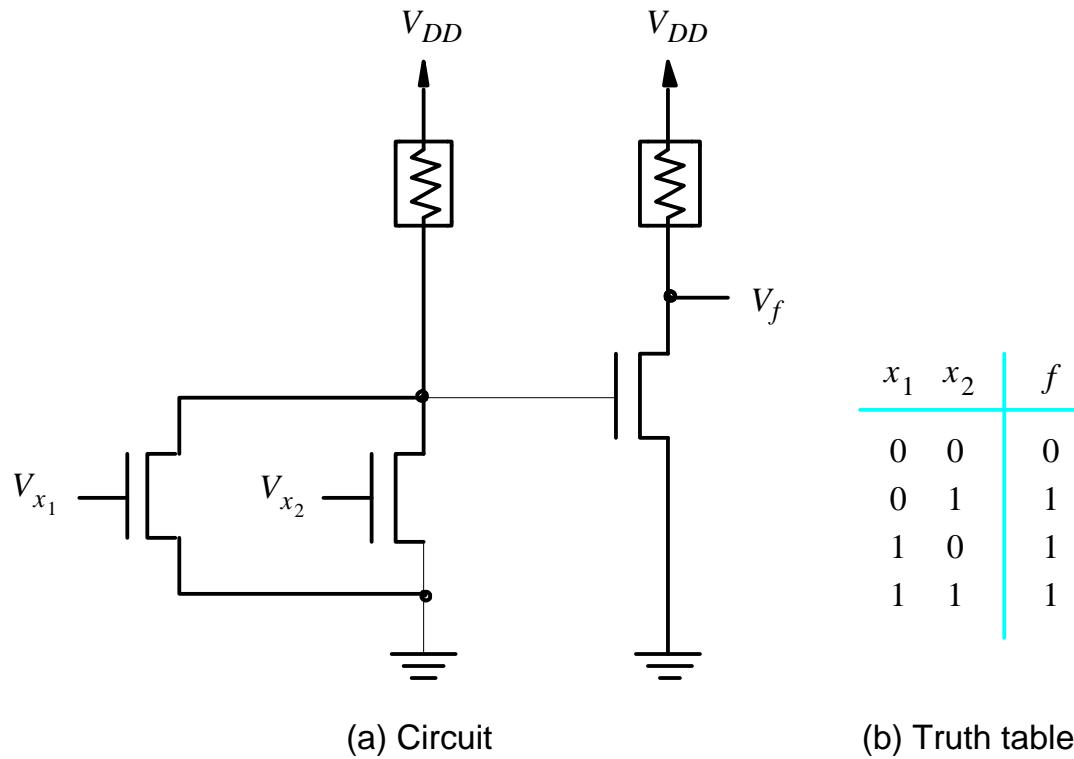
$x_1$	$x_2$	$f$
0	0	0
0	1	0
1	0	0
1	1	1

(b) Truth table



(c) Graphical symbols

Figure 3.8. NMOS realization of an AND gate.



(c) Graphical symbols

Figure 3.9. NMOS realization of an OR gate.

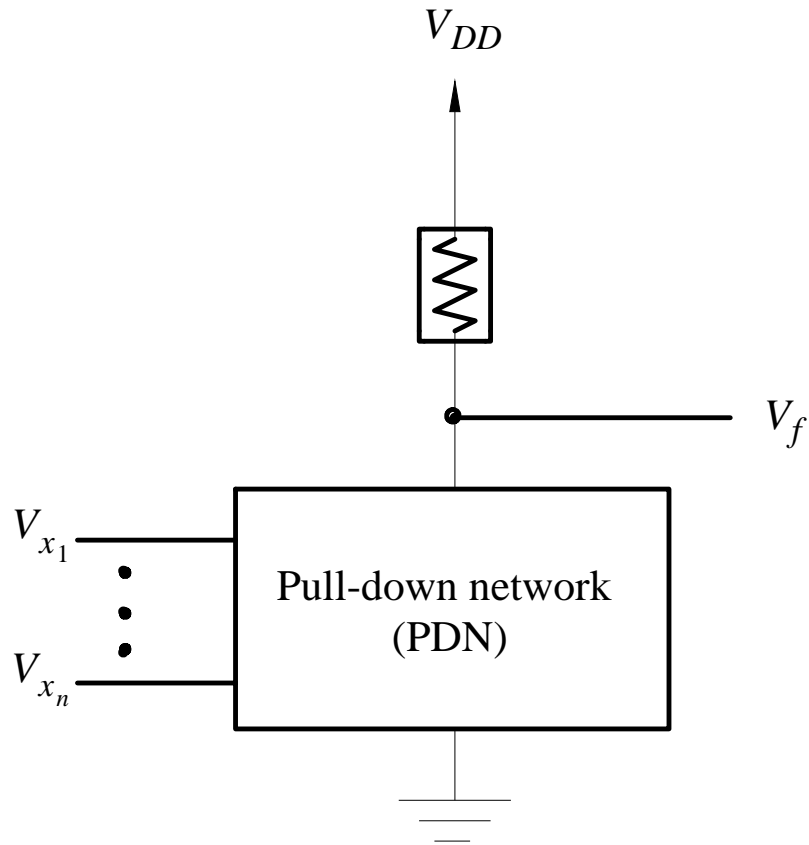


Figure 3.10. Structure of an NMOS circuit.

O conceito de circuitos CMOS é baseado na troca do dispositivo “pull-up” (resistores ligados ao  $V_{CC}$ ) por transistores PMOS

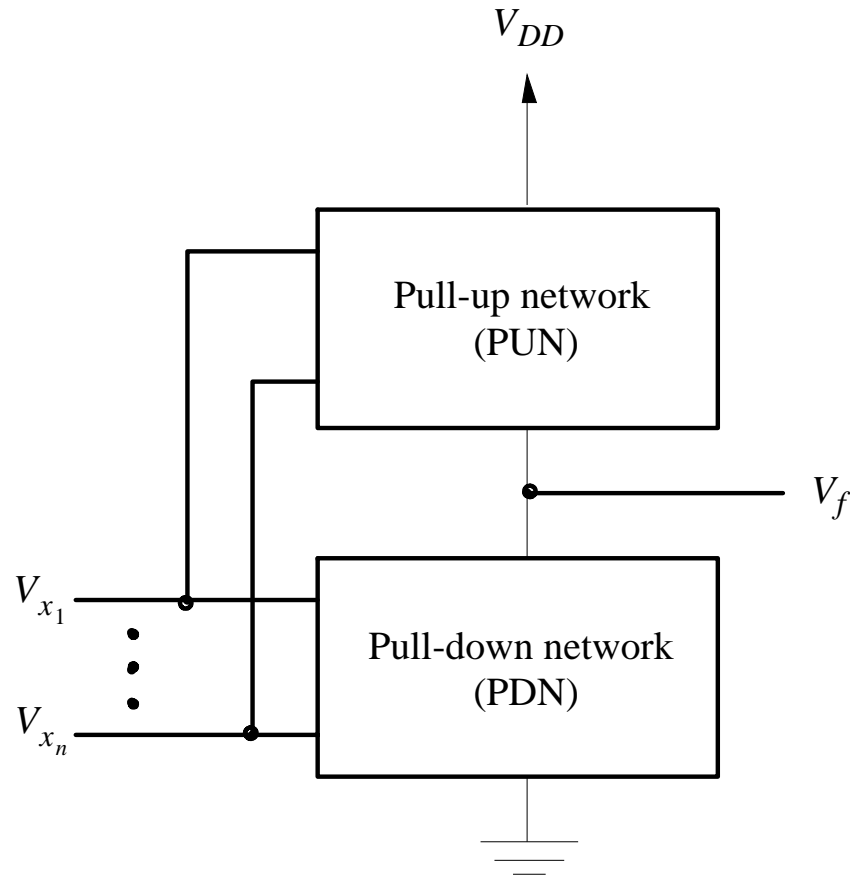
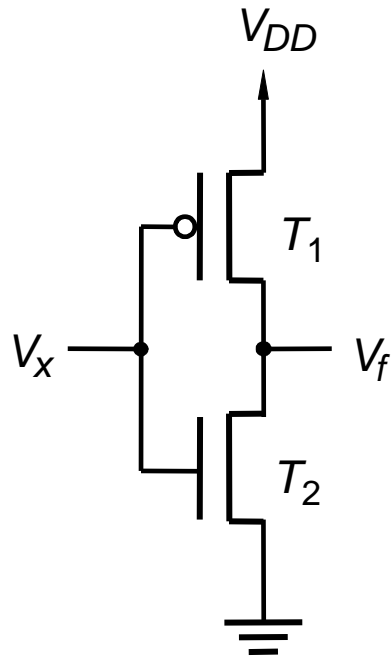


Figure 3.11. Structure of a CMOS circuit.

# *Implementação com CMOS*

- PDN e PUN têm a mesma quantidade de transistores, arrançados de modo que haja uma dualidade entre as redes
- Sempre que PDN tiver transistores em série, a PUN terá transistores em paralelo e vice-versa
- Sob condições estáticas não há corrente fluindo entre o  $V_{DD}$  e o Gnd

# Porta NOT com CMOS



(a) Circuit

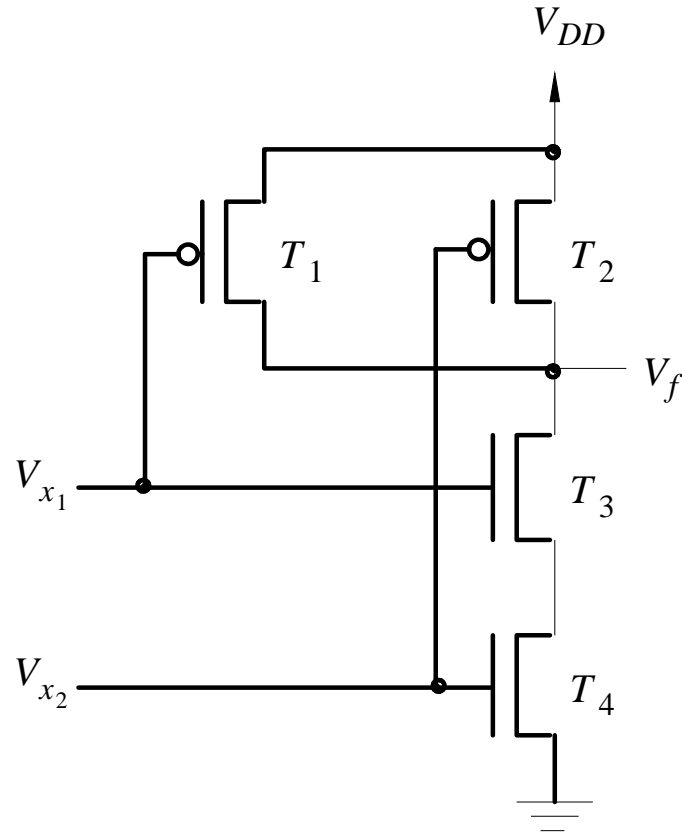
*Qual a vantagem de se utilizar CMOS?*

$x$	$T_1$	$T_2$	$f$
0	on	off	1
1	off	on	0

(b) Truth table and transistor states

Figure 3.12. CMOS realization of a NOT gate.



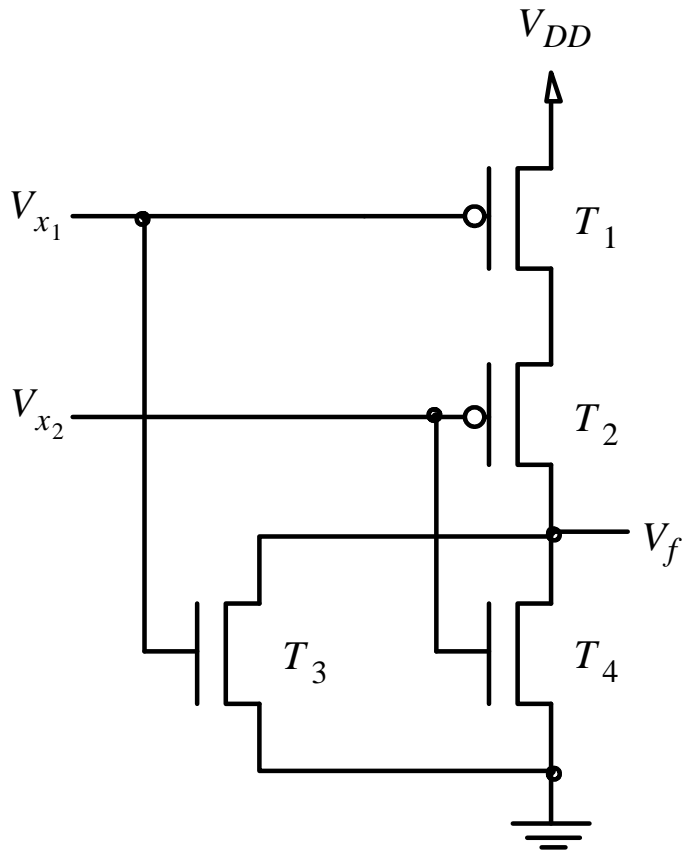


(a) Circuit

$x_1$	$x_2$	$T_1$	$T_2$	$T_3$	$T_4$	$f$
0	0	on	on	off	off	1
0	1	on	off	off	on	1
1	0	off	on	on	off	1
1	1	off	off	on	on	0

(b) Truth table and transistor states

Figure 3.13. CMOS realization of a NAND gate.



(a) Circuit

$x_1$	$x_2$	$T_1$	$T_2$	$T_3$	$T_4$	$f$
0	0	on	on	off	off	1
0	1	on	off	off	on	0
1	0	off	on	on	off	0
1	1	off	off	on	on	0

(b) Truth table and transistor states

Figure 3.14. CMOS realization of a NOR gate.

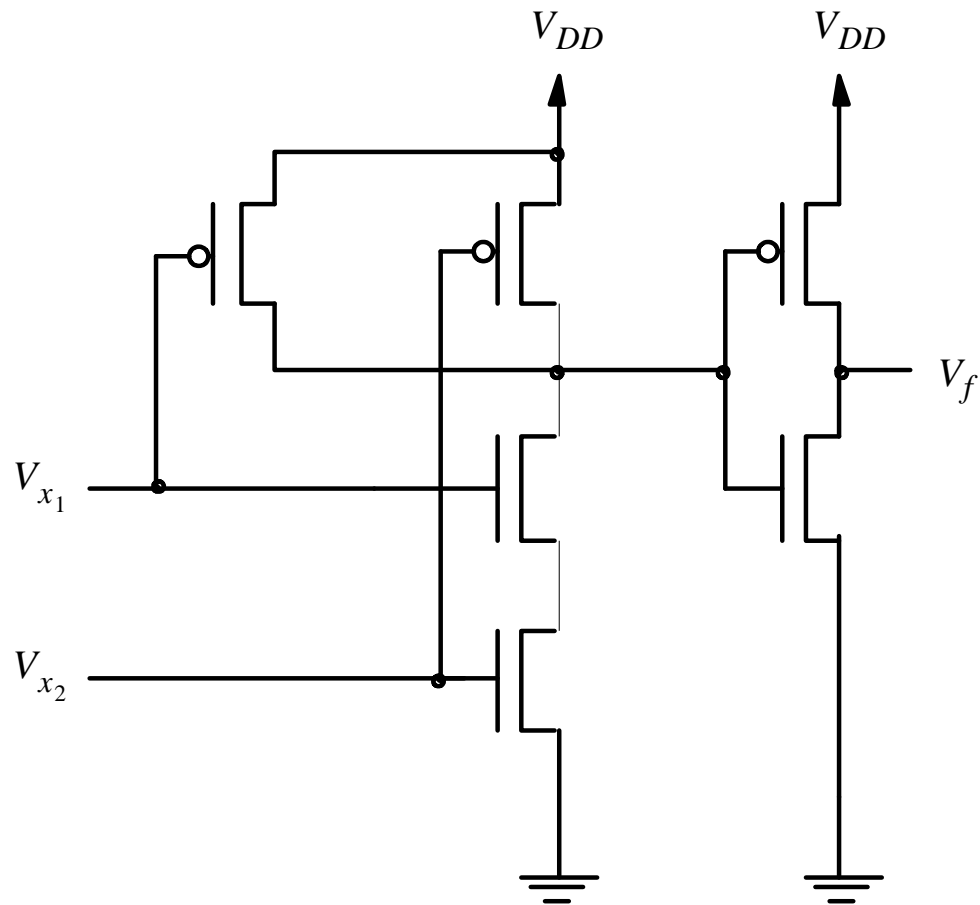


Figure 3.15. CMOS realization of an AND gate.

$$f = \overline{x_1} + \overline{x_2} \cdot \overline{x_3}$$

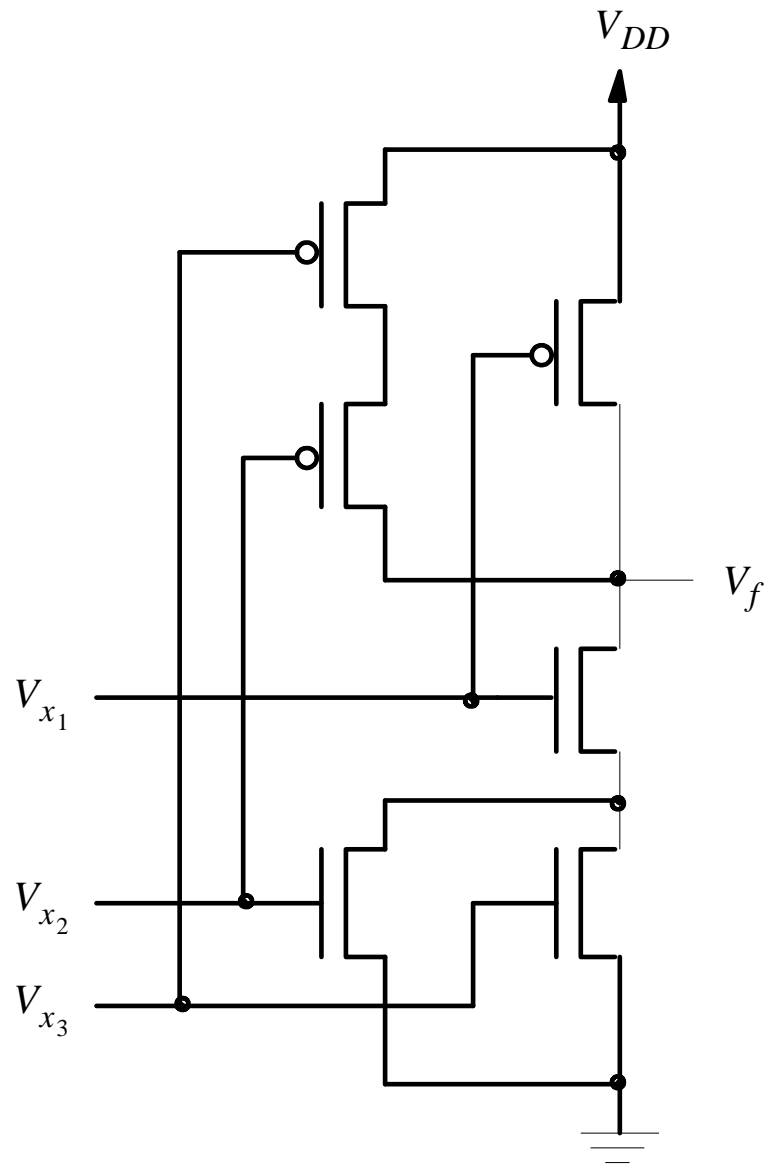
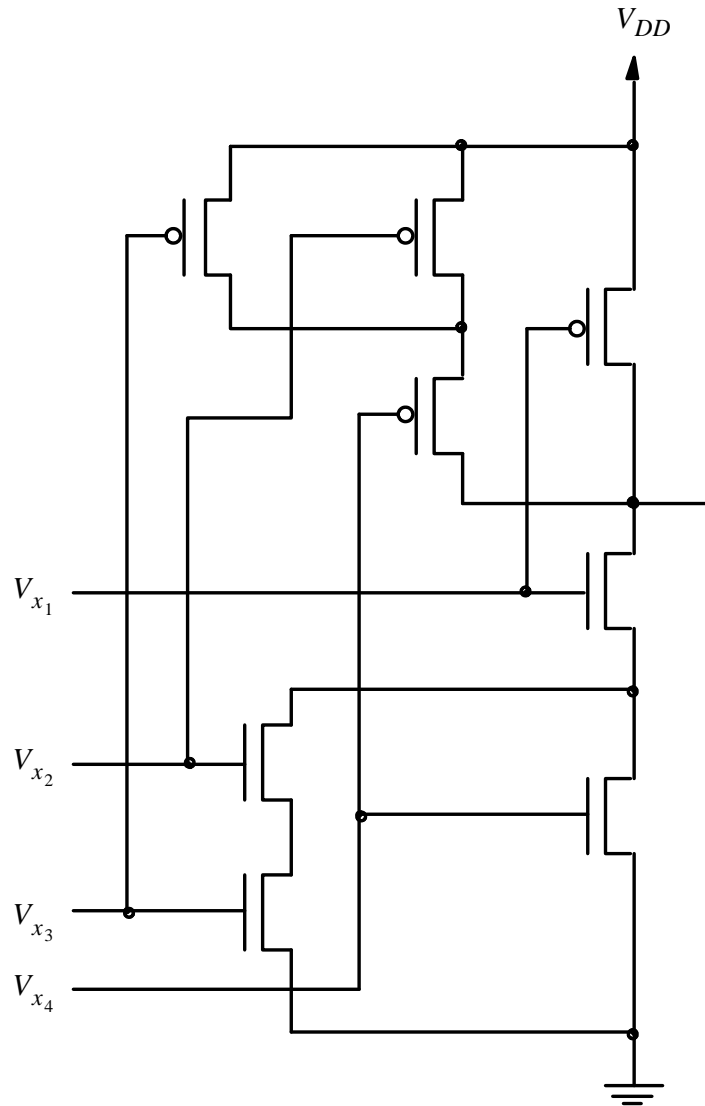


Figure 3.16. The circuit for Example 3.1.

- Construa o circuito CMOS para a seguinte função

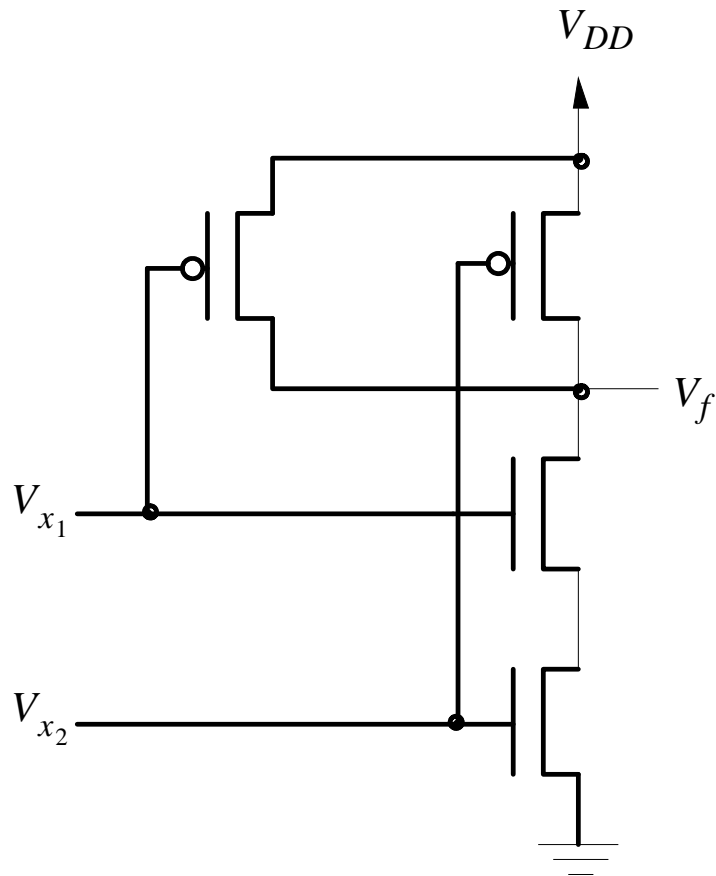
$$f = \bar{x}_1 + (\bar{x}_2 + \bar{x}_3) \bar{x}_4$$

## *Resposta do exercício anterior*



*Note que é possível construir circuitos relativamente complexos usando a combinação de transistores em paralelo e em série, sem necessariamente implementar cada conexão paralela ou serial como portas AND ou OR completas*

Figure 3.17. The circuit for Example 3.2.



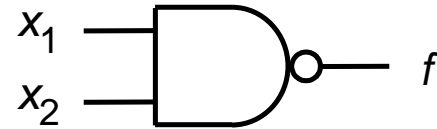
(a) Circuit

$V_{x_1}$	$V_{x_2}$	$V_f$
L	L	H
L	H	H
H	L	H
H	H	L

(b) Voltage levels

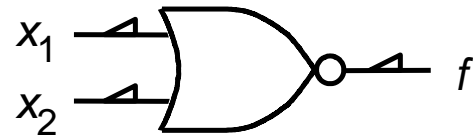
Figure 3.18. Voltage levels in the circuit in Figure 3.13.

$x_1$	$x_2$	$f$
0	0	1
0	1	1
1	0	1
1	1	0



(a) Positive logic truth table and gate symbol

$x_1$	$x_2$	$f$
1	1	0
1	0	0
0	1	0
0	0	1



(b) Negative logic truth table and gate symbol

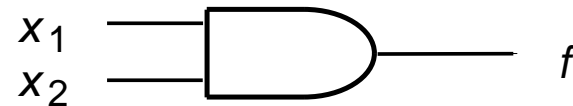
Figure 3.19. Interpretation of the circuit in Figure 3.18.



$V_{x_1}$	$V_{x_2}$	$V_f$
L	L	L
L	H	L
H	L	L
H	H	H

(a) Voltage levels

$x_1$	$x_2$	$f$
0	0	0
0	1	0
1	0	0
1	1	1



(b) Positive logic

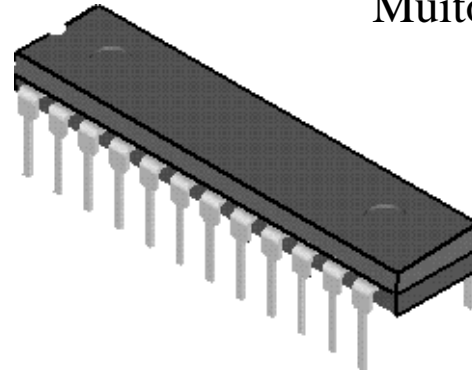
$x_1$	$x_2$	$f$
1	1	1
1	0	1
0	1	1
0	0	0



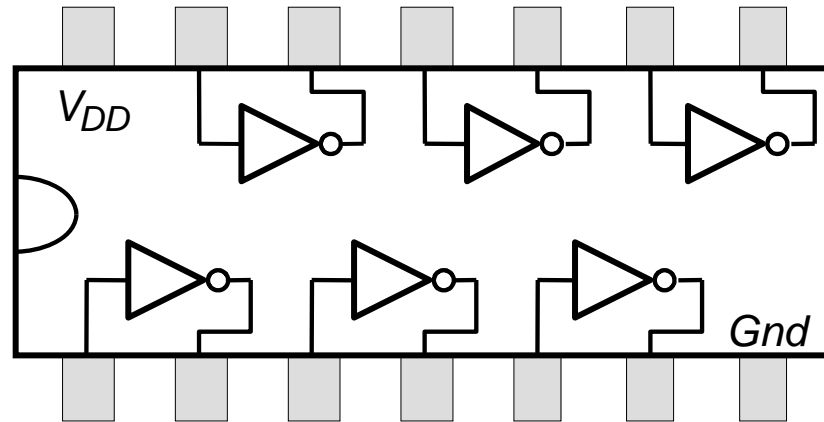
(c) Negative logic

Figure 3.20. Interpretation of the circuit in Figure 3.15.

Muito usado até meados de 1980



(a) Dual-inline package (DIP)



(b) Structure of 7404 chip

Figure 3.21. A 7400-series chip.

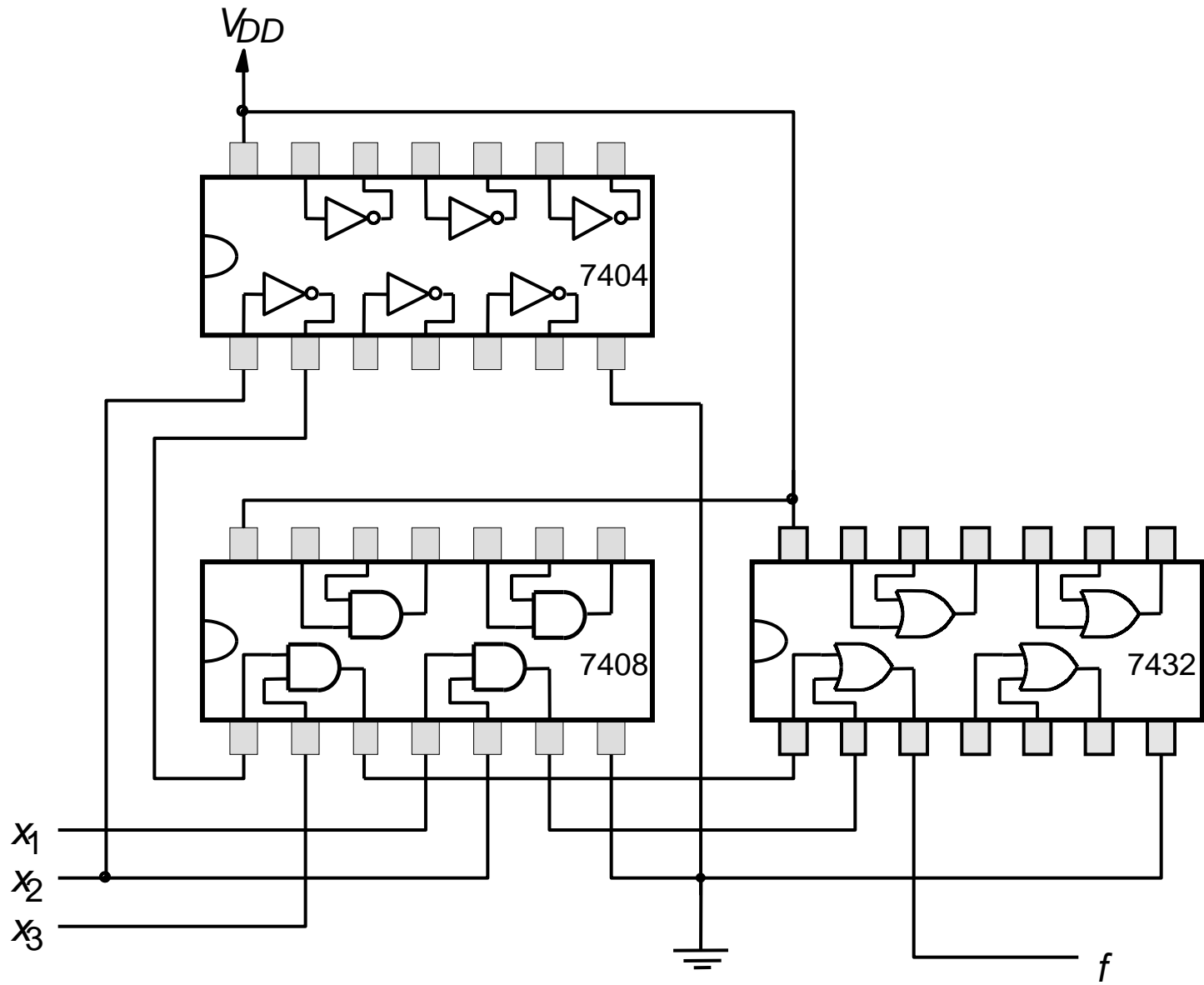


Figure 3.22. An implementation of  $f = x_1x_2 + \bar{x}_2x_3$ .

## Buffer tri-state

Buffers são normalmente utilizados para aumentar a velocidade dos circuitos

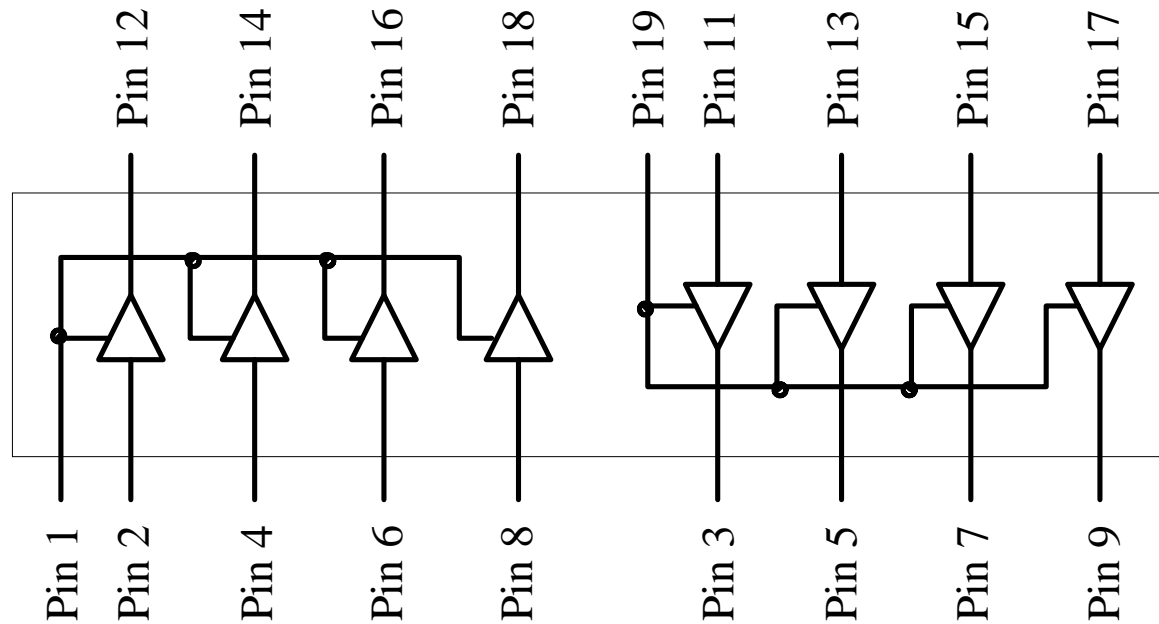


Figure 3.23. The 74244 buffer chip.

# Avanço dos CIs

- SSI (Small-Scale Integration)
- MSI (Medium-Scale Integration)
  - Entre 10 e 100 portas lógicas
- LSI (Large-Scale Integration)
- VLSI (Very Large Scale Integration)
  - Milhões/Bilhões de transistores
  - Essa é a tecnologia mais utilizada atualmente

# Processos usados pela Intel

- Intel® Itanium® com 2 bilhões de transistores

Process Name	<u>P1264</u>	<u>P1266</u>	<u>P1268</u>	<u>P1270</u>	<u>P1272</u>
Lithography	65nm	45nm	32nm	22nm	16nm
1 <sup>st</sup> Production	2005	2007	2009	2011	2013

